New Jersey Semi-Conductor Products, Inc.

20 STERN AVE. SPRINGFIELD, NEW JERSEY 07081 U.S.A.

# **TIP47, TIP48, TIP50**

## High Voltage NPN Silicon Power Transistors

This series is designed for line operated audio output amplifier, SWITCHMODE power supply drivers and other switching applications.

#### Features

- Popular TO-220 Plastic Package
- These Devices are Pb–Free and are RoHS Compliant\*
- Complementary to the MJE5730 and MJE5731 Series

#### MAXIMUM RATINGS

| Rating  | Symbol                            | TIP47        | TIP48 | TIP50     | Unit      |
|---|-----------------------------------|--------------|-------|-----------|-----------|
| Collector - Emitter Voltage   | V <sub>CEO</sub>                  | 250          | 300   | 400       | Vdc       |
| Collector - Base Voltage  | V <sub>CB</sub>                   | 350          | 400   | 500       | Vdc       |
| Emitter – Base Voltage  | V <sub>EB</sub>                   | 5.0          |       |           | Vdc       |
| Collector Current – Continuous  | lc                                | 1.0          |       |           | Adc       |
| Collector Current – Peak  | I <sub>СМ</sub>                   | 2.0          |       |           | Adc       |
| Base Current  | ۱ <sub>B</sub>                    | 0.6          |       |           | Adc       |
| Total Power Dissipation<br>@ T <sub>C</sub> = 25°C<br>Derate above 25°C | PD                                | 40<br>0.32   |       |           | W<br>W/°C |
| Total Power Dissipation<br>@ T <sub>C</sub> = 25°C<br>Derate above 25°C | PD                                | 2.0<br>0.016 |       | W<br>W/°C |           |
| Unclamped Inducting Load<br>Energy (See Figure 8)                       | E                                 | 20           |       |           | mJ        |
| Operating and Storage<br>Junction Temperature Range                     | T <sub>J</sub> , T <sub>stg</sub> | –65 to +150  |       |           | °C        |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### **THERMAL CHARACTERISTICS**

| Characteristic                             | Symbol           | Max   | Unit |
|--|------------------|-------|------|
| Thermal Resistance,<br>Junction-to-Case    | R <sub>θJC</sub> | 3.125 | °C/W |
| Thermal Resistance,<br>Junction-to-Ambient | $R_{\theta JA}$  | 62.5  | °C/W |

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### 1.0 AMPERE POWER TRANSISTORS NPN SILICON 250-300-400 VOLTS 40 WATTS









NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

## **Quality Semi-Conductors**

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = $25^{\circ}$ C unless otherwise noted)

| Characteristic   |                         | Symbol                | Min               | Max               | Unit |
|--|-------------------------|-----------------------|-------------------|-------------------|------|
| OFF CHARACTERISTICS  |                         |                       |                   |                   |      |
| Collector-Emitter Sustaining Voltage (Note 1)<br>( $I_C = 30$ mAdc, $I_B = 0$ )  | TIP47<br>TIP48<br>TIP50 | V <sub>CEO(sus)</sub> | 250<br>300<br>400 | _<br>_<br>_       | Vdc  |
|  | TIP47<br>TIP48<br>TIP50 | I <sub>CEO</sub>      | -<br>-<br>-       | 1.0<br>1.0<br>1.0 | mAdc |
| Collector Cutoff Current<br>$(V_{CE} = 350 \text{ Vdc}, V_{BE} = 0)$<br>$(V_{CE} = 400 \text{ Vdc}, V_{BE} = 0)$<br>$(V_{CE} = 500 \text{ Vdc}, V_{BE} = 0)$ | TIP47<br>TIP48<br>TIP50 | I <sub>CES</sub>      |                   | 1.0<br>1.0<br>1.0 | mAdc |
| Emitter Cutoff Current<br>( $V_{BE} = 5.0 \text{ Vdc}, I_C = 0$ )  |                         | I <sub>EBO</sub>      | -                 | 1.0               | mAdc |
| ON CHARACTERISTICS (Note 1)  |                         |                       |                   |                   |      |
|  |                         | h <sub>FE</sub>       | 30<br>10          | 150<br>-          | -    |
| Collector–Emitter Saturation Voltage $(I_{C} = 1.0 \text{ Adc}, I_{B} = 0.2 \text{ Adc})$  |                         | V <sub>CE(sat)</sub>  | -                 | 1.0               | Vdc  |
| Base-Emitter On Voltage<br>(I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 10 Vdc)  |                         | V <sub>BE(on)</sub>   | _                 | 1.5               | Vdc  |
| DYNAMIC CHARACTERISTICS  |                         |                       |                   |                   |      |
| Current–Gain – Bandwidth Product<br>( $I_C = 0.1 \text{ Adc}, V_{CE} = 10 \text{ Vdc}, f = 2.0 \text{ MHz}$ )  |                         | f <sub>T</sub>        | 10                | -                 | MHz  |
| Small–Signal Current Gain<br>(I <sub>C</sub> = 0.2 Adc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)   |                         | h <sub>fe</sub>       | 25                | -                 | -    |

1. Pulse Test: Pulse width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.